

Phase Control Thyristors (Hockey PUK Version), 500 A



A-PUK (TO-200AB)

PRIMARY CHARACTERISTICS					
I _{T(AV)}	500 A				
V _{DRM} /V _{RRM}	400 V, 600 V				
V_{TM}	1.35 V				
I _{GT}	90 mA				
T_J	-40 °C to +150 °C				
Package	A-PUK (TO-200AB)				
Circuit configuration	Single SCR				

FEATURES

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-PUK (TO-200AB)



- Extended temperature range
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		500	A			
I _{T(AV)}	T _{hs}	80	°C			
1		1130	Α			
I _T (RMS)	T _{hs}	25	°C			
1	50 Hz	7200	A			
ITSM	60 Hz	7500	A			
l ² t	50 Hz	260	kA ² s			
I-I	60 Hz	230	KA-S			
V _{DRM} /V _{RRM}		400 to 600	V			
tq	Typical	100	μs			
TJ		-40 to 150	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA				
VC CTOOCH C	04	400 500		75				
VS-ST280CHC 06		600	700	/5				



ABSOLUTE MAXIMUM RATINGS	S					
PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	L	180° condu	180° conduction, half sine wave			Α
at heatsink temperature	$I_{T(AV)}$	double side	(single side) co	oled	80 (110)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink tempe	erature double side cooled	1130	
		t = 10 ms	No voltage		7200	A kA ² s
Maximum peak, one-cycle	L	t = 8.3 ms	reapplied		7500	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}	Sinusoidal half wave, initial $T_J = T_J$ maximum	6000	
		t = 8.3 ms	reapplied		6300	
Maximum I ² t for fusing	l ² t	t = 10 ms	No voltage		260	
		t = 8.3 ms	reapplied		235	
		t = 10 ms	100 % V _{RRM}		180	
		t = 8.3 ms	reapplied		165	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied			kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.84	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			V
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.47	11122
Maximum on-state voltage	V_{TM}	$I_{pk} = 1000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.35	V
Maximum holding current	I _H	T _ 05 °C	anada aunnis 1	2 V registive lead	600	mΛ
Maximum (typical) latching current	ΙL	T _J = 25 °C, anode supply 12 V resistive load 1000 (300)			1000 (300)	- mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ V_d 0.67 % V_{DRM} , $T_J = 25 ^{\circ}C$	1.0	- 19
Typical turn-off time	t _q	$\begin{array}{l} I_{TM}=300~A,~T_J=T_J~maximum,~dl/dt=20~A/\mu s,\\ V_R=50~V,~dV/dt=20~V/\mu s,~gate~0~V~100~\Omega,~t_p=500~\mu s \end{array}$	100	μs

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNIT S		
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs		
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	75	mA		



TRIGGERING							
PARAMETER	SYMBOL	TE	TEGT CONDITIONS		VALUES		
PANAMETEN	STINIBUL	''	ST CONDITIONS	TYP.	MAX.	UNITS	
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10	0.0	W	
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV	
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	3	.0	Α	
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J \text{ maximum, } t_p \le 5 \text{ ms}$		0	V		
Maximum peak negative gate voltage	- V _{GM}	rj = rj maximum,	5.0		V		
DC gate current required to trigger	I _{GT}	T _J = - 40 °C		180	-		
		T _J = 25 °C		90	150	mA	
		T _J = 150 °C	Maximum required gate trigger/ current/voltage are the lowest		-		
		T _J = - 40 °C	value which will trigger all units 12 V anode to cathode applied	2.9	-		
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	12 v anode to cathode applied	1.8	3.0	V	
		T _J = 150 °C		1.0	-		
DC gate current not to trigger	I _{GD}	T. T. magyimay ma	Maximum gate current/voltage not to trigger is the maximum	1	0	mA	
DC gate voltage not to trigger	V _{GD}	$T_J = T_J \text{ maximum}$	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.	30	V	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction and storage temperature range	T _J , T _{Stg}		- 40 to 150	°C		
Maximum thermal resistance,	В	DC operation single side cooled	0.17			
junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.08	K/W		
Maximum thermal resistance,	В	DC operation single side cooled	0.033	T N VV		
case to heatsink	R _{thC-hs}	DC operation double side cooled	0.017			
Mounting force, ± 10 %			4900 (500)	N (kg)		
Approximate weight			50	g		
Case style		See dimensions - link at the end of datasheet A-PUK (TO-200		200AB)		

ΔR_{thJ-hs} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULAR	CONDUCTION	TEST CONDITIONS	UNITS
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS
180°	0.016	0.017	0.011	0.011	$T_J = T_J$ maximum	
120°	0.019	0.019	0.019	0.019		K/W
90°	0.024	0.024	0.026	0.026		
60°	0.035	0.035	0.036	0.037		
30°	0.060	0.060	0.060	0.061		

Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC



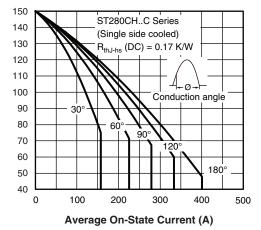


Fig. 1 - Current Ratings Characteristics

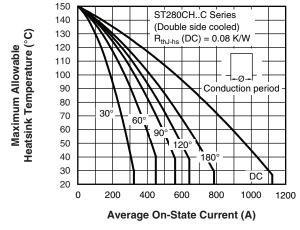


Fig. 4 - Current Ratings Characteristics

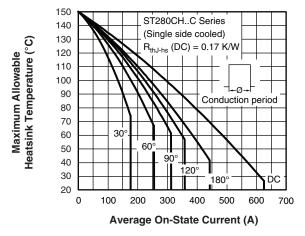


Fig. 2 - Current Ratings Characteristics

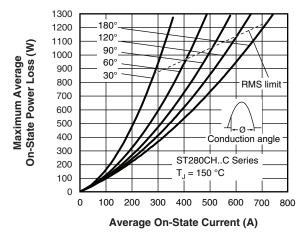


Fig. 5 - On-State Power Loss Characteristics

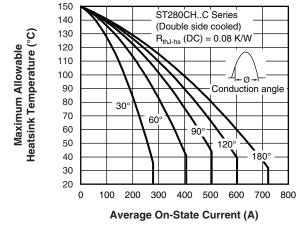


Fig. 3 - Current Ratings Characteristics

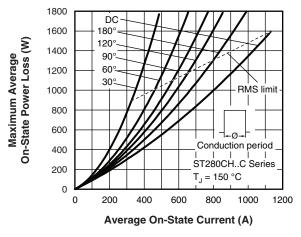


Fig. 6 - On-State Power Loss Characteristics

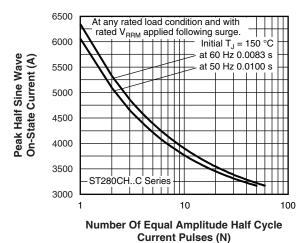


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

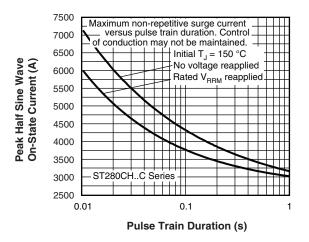


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

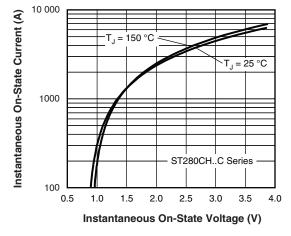


Fig. 9 - On-State Voltage Drop Characteristics

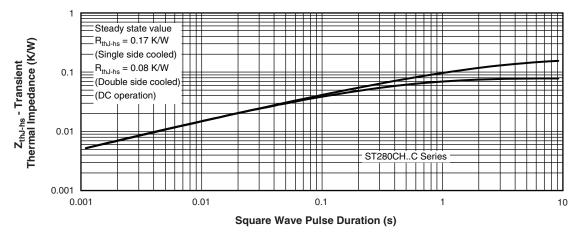


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

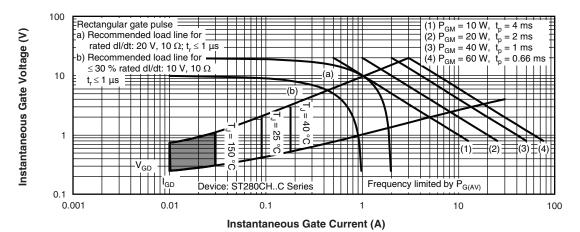
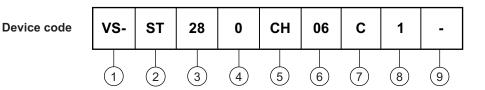


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE



Vishay Semiconductors product

Thyristor

Essential part number

0 = converter grade

CH = ceramic PUK, high temperature

Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

C = PUK case A-PUK (TO-200AB)

0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

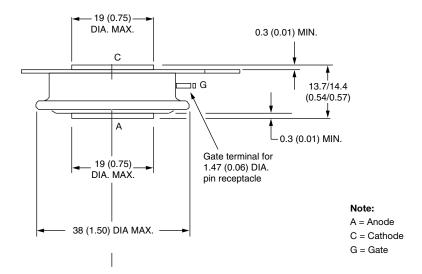
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95074			

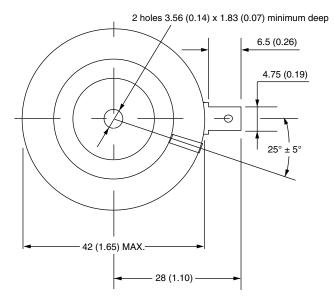


A-PUK (TO-200AB)

DIMENSIONS in millimeters (inches)

Anode to gate Creepage distance: 7.62 (0.30) minimum Strike distance: 7.12 (0.28) minimum





Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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